

IN THE CLAIMS:

Please amend claims 12, 49, 57, 65 and 73 as follows:

1. (Withdrawn) A process for producing a light emitting device comprising the steps of:

forming an anode;

wiping/cleaning the surface of the anode with a wiping/cleaning material.

forming an organic compound layer on the anode after wiping/cleaning the surface of thereof; and

forming a cathode on the organic compound layer.

2. (Withdrawn) The process for producing the light emitting device according to claim 1, wherein the anode is composed of a transparent conductive film.

3. (Withdrawn) The process for producing the light emitting device according to claim 1, wherein the surface is made flat by the wiping/cleaning.

4. (Withdrawn) The process for producing the light emitting device according to claim 1, wherein the wiping/cleaning material is a PVA-based porous body.

5. (Withdrawn) The process for producing the light emitting device according to claim 1, wherein the surface is wiped/cleaned with the wiping/cleaning material and a washing liquid.

6. (Withdrawn) The process for producing the light emitting device according to claim 1, wherein the surface is scrubbed with the wiping/cleaning material.

7. (Withdrawn) The process for producing the light emitting device according to claim 1, wherein when contact angle to the anode surface is smaller than 90° before the wiping/cleaning, the contact angle after the wiping/cleaning is larger than the contact angle before the wiping/cleaning and is smaller than 90° .

8. (Withdrawn) A process for producing an active matrix type light emitting device comprising the steps of:

forming TFTs over a substrate;

forming a first insulating film comprising organic resin material over the TFTs;

forming a second insulating film comprising inorganic insulating material on the first insulating film;

forming a transparent conductive film on the second insulating film; and

wiping/cleaning the surface of the transparent conductive film with a wiping/cleaning material.

9. (Original) A process for producing an active matrix type light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising organic resin material over the thin film transistor;

forming a second insulating film comprising inorganic insulating material on the first insulating film;

forming an anode on the second insulating film; and

wiping and cleaning the surface of the anode with a wiping and cleaning material.

10. (Previously Amended) The process for producing the active matrix type light emitting device according to claim 8, wherein the surface of the anode is made flat by the wiping and cleaning material.

11. (Original) The process for producing the active matrix type light emitting device according to claim 8, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

12. (Currently Amended) The process for producing the active matrix type light emitting device according to claim 8, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, and silicon nitride oxide, ~~aluminum nitride, aluminum nitride oxide and aluminum oxide nitride.~~

13. (Previously Amended) The process for producing the active matrix type light emitting device according to claim 8, wherein the wiping and cleaning material is a PVA-based porous body.

14. (Previously Amended) The process for producing the active matrix type light emitting device according to claim 8, wherein the anode is wiped and cleaned with the wiping and cleaning material and a washing liquid.

15. (Previously Amended) The process for producing the active matrix type light emitting device according to claim 8, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

16. (Previously Amended) The process for producing the active matrix type light emitting device according to claim 8, wherein when contact angle to the surface of the anode is smaller than 90° before the wiping and cleaning, the contact angle after the

wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90° .

17. (Withdrawn) A process for producing a light emitting device comprising the steps of:

forming a transparent conductive film;

forming an insulating film comprising an organic resin material on the transparent conductive film; and

wiping/cleaning the surface of the insulating film with a wiping/cleaning material.

18. (Withdrawn) A process for producing a light emitting device comprising the steps of:

forming an anode;

forming an insulating film comprising an organic resin material on the anode; and

wiping/cleaning the surface of the insulating film with a wiping/cleaning material.

19. (Withdrawn) The process for producing the light emitting device according to claim 17, wherein the surface of the insulating film is made flat by the wiping/cleaning.

20. (Withdrawn) The process for producing the light emitting device according to claim 17, wherein the wiping/cleaning material is a PVA-based porous body.

21. (Withdrawn) The process for producing the light emitting device according to claim 17, wherein the surface of the insulating film is wiped/cleaned with the wiping/cleaning material and a washing liquid.

22. (Withdrawn) The process for producing the light emitting device according to claim 17, wherein the surface of the insulating film is scrubbed with the wiping/cleaning material.

23. (Withdrawn) The process for producing the light emitting device according to claim 17, wherein when contact angle to the insulating film is smaller than 90° before the wiping/cleaning, the contact angle after the wiping/cleaning is larger than the contact angle before the wiping/cleaning and is smaller than 90° .

24. (Withdrawn) The process for producing the light emitting device according to claim 17, wherein the insulating film is formed to have a film thickness of 1 to 50 nm.

25. (Withdrawn) The process for producing the light emitting device according to claim 17, wherein the insulating film comprises a material selected from the group consisting of polyacrylate, polyimide or polyamide.

26. (Withdrawn) A process for producing an active matrix type light emitting device comprising the steps of:

forming TFTs over a substrate;

forming a first insulating film comprising an organic resin material over the TFTs;

forming a second insulating film comprising an inorganic insulating material on the first insulating film;

forming a transparent conductive film on the second insulating film;

forming a third insulating film comprising an organic resin material on the transparent conductive film; and

wiping/cleaning the surface of the third insulating film with a wiping/cleaning material.

27. (Original) A process for producing an active matrix type light emitting device comprising the steps of:

forming TFTs over a substrate;

forming a first insulating film comprising an organic resin material over the TFTs;

forming a second insulating film comprising an inorganic insulating material on the first insulating film;

forming an anode on the second insulating film;

forming a third insulating film comprising an organic resin material on the anode; and

wiping/cleaning the surface of the third insulating film with a wiping/cleaning material.

28. (Withdrawn) The process for producing the light emitting device according to claim 26, wherein the surface of the third insulating film is made flat by the wiping/cleaning.

29. (Withdrawn) The process for producing the light emitting device according to claim 26, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

30. (Withdrawn) The process for producing the light emitting device according to claim 26, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, silicon nitride oxide, aluminum nitride, aluminum nitride oxide and aluminum oxide nitride.

31. (Withdrawn) The process for producing the light emitting device according to claim 26, wherein the wiping/cleaning material is a PVA-based porous body.

32. (Withdrawn) The process for producing the light emitting device according to claim 26, wherein the transparent conductive film is wiped/cleaned with the wiping/cleaning material and a washing liquid.

33. (Withdrawn) The process for producing the light emitting device according to claim 26, wherein the surface of the third insulating film is scrubbed with the wiping/cleaning material.

34. (Withdrawn) The process for producing the light emitting device according to claim 26, wherein the third insulating film is formed to have a film thickness of 1 to 50 nm.

35. (Withdrawn) The process for producing the light emitting device according to claim 26, wherein the third insulating film is made of polyacrylate, polyimide or polyamide.

36. (Withdrawn) The process for producing the light emitting device according to claim 26, wherein when contact angle to the surface of the third insulating film is smaller than 90° before the wiping/cleaning, the contact angle after the wiping/cleaning

is larger than the contact angle before the wiping/cleaning and is smaller than 90° .

37. (Withdrawn) The process for producing the light emitting device according to claim 26, wherein the TFT is manufactured by following steps:

first step of forming a semiconductor layer over the substrate;

second step of forming an insulating film on the semiconductor layer;

third step of forming a conductive layer on the insulating film;

fourth step of selectively etching the conductive layer to form a first conductive layer having a first tapered shape;

fifth step of introducing an impurity element into the semiconductor layer;

sixth step of selectively etching the tapered shape; and

seventh step of introducing the e first conductive layer to form a second conductive layer having a second impurity element into the semiconductor layer,

wherein the concentration of the impurity element introduced in the seventh step is lower than that introduced in the fifth step.

38. (Withdrawn) A process for producing an active matrix type light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising organic resin material over the thin film transistor;

forming a second insulating film comprising inorganic insulating material on the first insulating film;

forming a transparent conductive film formed on the second insulating film;

patterning the transparent conductive film to form an anode; and

wiping and cleaning the surface of the anode with a wiping and cleaning material.

39. (Withdrawn) The process for producing the active matrix type light emitting device according to claim 38, wherein the surface of the anode is made flat by the wiping and cleaning material.

40. (Withdrawn) The process for producing the active matrix type light emitting device according to claim 38, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

41. (Withdrawn) The process for producing the active matrix type light emitting device according to claim 38, wherein the

inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, silicon nitride oxide, aluminum nitride, aluminum nitride oxide and aluminum oxide nitride.

42. (Withdrawn) The process for producing the active matrix type light emitting device according to claim 38, wherein the wiping and cleaning material is a PVA-based porous body.

43. (Withdrawn) The process for producing the active matrix type light emitting device according to claim 38, wherein the anode is wiping and cleaning with the wiping and cleaning material and a washing liquid.

44. (Withdrawn) The process for producing the active matrix type light emitting device according to claim 38, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

45. (Withdrawn) The process for producing the active matrix type light emitting device according to claim 38, wherein when contact angle to the surface of the anode is smaller than 90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90° .

46. (Previously Added) A process for producing an active matrix light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising organic resin material over the thin film transistor;

forming a second insulating film comprising inorganic material on the first insulating film;

forming an electrode connected to the thin film transistor on the second insulating film;

forming an anode formed on the electrode and the second insulating film; and

wiping and cleaning the surface of the anode with a wiping and cleaning material.

47. (Previously Added) The process for producing the active matrix type light emitting device according to claim 46, wherein the surface of the anode is made flat by the wiping and cleaning material.

48. (Previously Added) The process for producing the active matrix type light emitting device according to claim 46, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

49. (Currently Amended) The process for producing the active matrix type light emitting device according to claim 46, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, and silicon nitride oxide, ~~aluminum nitride, aluminum nitride oxide and aluminum oxide nitride.~~

50. (Previously Added) The process for producing the active matrix type light emitting device according to claim 46, wherein the wiping and cleaning material is a PVA-based porous body.

51. (Previously Added) The process for producing the active matrix type light emitting device according to claim 46, wherein the anode is wiping and cleaning with the wiping and cleaning material and a washing liquid.

52. (Previously Added) The process for producing the active matrix type light emitting device according to claim 46, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

53. (Previously Added) The process for producing the active matrix type light emitting device according to claim 46, wherein when contact angle to the surface of the anode is smaller than 90° before the wiping and cleaning, the contact angle after the

wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90° .

54. (Previously Added) A process for producing an active matrix type light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising organic resin material over the thin film transistor;

forming a second insulating film comprising inorganic insulating material on the first insulating film;

forming an anode on the second insulating film;

wiping and cleaning the surface of the anode with a wiping and cleaning material; and

forming an organic compound layer on the wiped and cleaned surface of the anode.

55. (Previously Added) The process for producing the active matrix type light emitting device according to claim 54, wherein the surface of the anode is made flat by the wiping and cleaning material.

56. (Previously Added) The process for producing the active matrix type light emitting device according to claim 54, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

57. (Currently Amended) The process for producing the active matrix type light emitting device according to claim 54, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, and silicon nitride oxide, ~~aluminum nitride, aluminum nitride oxide and aluminum oxide nitride.~~

58. (Previously Added) The process for producing the active matrix type light emitting device according to claim 54, wherein the wiping and cleaning material is a PVA-based porous body.

59. (Previously Added) The process for producing the active matrix type light emitting device according to claim 54, wherein the anode is wiping and cleaning with the wiping and cleaning material and a washing liquid.

60. (Previously Added) The process for producing the active matrix type light emitting device according to claim 54, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

61. (Previously Added) The process for producing the active matrix type light emitting device according to claim 54, wherein when contact angle to the surface of the anode is smaller than

90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.

62. (Previously Added) A process for producing an active matrix type light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film over the thin film transistor;

forming a second insulating film on the first insulating film;

forming an anode on the second insulating film; and

wiping and cleaning the surface of the anode with a wiping and cleaning material.

63. (Previously Added) The process for producing the active matrix type light emitting device according to claim 62, wherein the surface of the anode is made flat by the wiping and cleaning material.

64. (Previously Added) The process for producing the active matrix type light emitting device according to claim 62, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

65. (Currently Amended) The process for producing the active matrix type light emitting device according to claim 62, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, and silicon nitride oxide, ~~aluminum nitride, aluminum nitride oxide and aluminum oxide nitride.~~

66. (Previously Added) The process for producing the active matrix type light emitting device according to claim 62, wherein the wiping and cleaning material is a PVA-based porous body.

67. (Previously Added) The process for producing the active matrix type light emitting device according to claim 62, wherein the anode is wiping and cleaning with the wiping and cleaning material and a washing liquid.

68. (Previously Added) The process for producing the active matrix type light emitting device according to claim 62, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

69. (Previously Added) The process for producing the active matrix type light emitting device according to claim 62, wherein when contact angle to the surface of the anode is smaller than 90° before the wiping and cleaning, the contact angle after the

wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.

70. (Previously Added) A process for producing an active matrix type light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film over the thin film transistor;

forming a second insulating film on the first insulating film;

forming an anode on the second insulating film;

wiping and cleaning the surface of the anode with a wiping and cleaning material; and

forming an organic compound layer on the wiped and cleaned surface of the anode.

71. (Previously Added) The process for producing the active matrix type light emitting device according to claim 70, wherein the surface of the anode is made flat by the wiping and cleaning material.

72. (Previously Added) The process for producing the active matrix type light emitting device according to claim 70, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

73. (Currently Amended) The process for producing the active matrix type light emitting device according to claim 70, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, and silicon nitride oxide, ~~aluminum nitride, aluminum nitride oxide and aluminum oxide nitride.~~

74. (Previously Added) The process for producing the active matrix type light emitting device according to claim 70, wherein the wiping and cleaning material is a PVA-based porous body.

75. (Previously Added) The process for producing the active matrix type light emitting device according to claim 70, wherein the anode is wiping and cleaning with the wiping and cleaning material and a washing liquid.

76. (Previously Added) The process for producing the active matrix type light emitting device according to claim 70, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

77. (Previously Added) The process for producing the active matrix type light emitting device according to claim 70, wherein when contact angle to the surface of the anode is smaller than

90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.